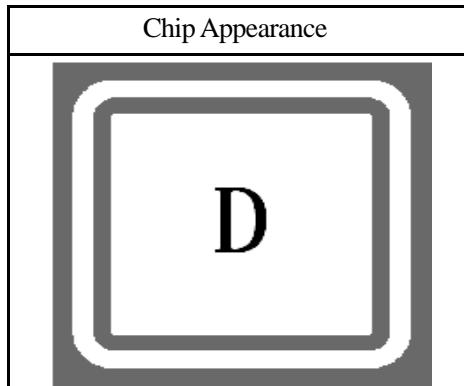


CRD140-XX



Die size (um×um)		820X820
Wafer thickness (um)		245±10
Bondpad size (um ²)	Drain(D)	542×542
Scribe line width(um)		60
Top		AG(5.5um)
Bottom		AG
Wafer Size		6"

Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	Value	Units	Note
Junction Temperature	T _j	125	°C	SOT89/T0126/T0252/T0220
Storage Temperature	T _{stg}	-40~125	°C	
Collector Dissipation	P _c	1.0	W	SOT89
		1.5	W	T0126
		1.5	W	T0252
		2.0	W	T0220

Electrical Characteristics (Ta=25°C)

Current Range	Constant Current (I _H)		Turn-on voltage (V _k)		Limiting ratio (K _c)	Withstand voltage (V)
	I _H	Voltage (V)	V _k (V)	I _k (mA)		
D140-A	5-8	10	≤3.5	0.8 I _H	<1.1	>140
D140-B	8.0-13	10	≤3.5	0.8 I _H	<1.1	>140
D140-C	13-18	10	≤3.5	0.8 I _H	<1.1	>140
D140-D	18-23	10	≤4.0	0.8 I _H	<1.1	>140
D140-E	23-28	20	≤4.0	0.8 I _H	<1.1	>140
D140-F	28-35	20	≤4.5	0.8 I _H	<1.1	>140
D140-G	35-45	20	≤4.5	0.8 I _H	<1.1	>140
